

# Transient Voltage Suppressor Diode

**BZA100**

18 Diode Array

6.8V/200mA

# DATASHEET

OEM – Philips

Source: Philips Databook 1999

**18-fold ESD transient voltage suppressor****BZA100****FEATURES**

- SO20 SMD package allows 18 separate voltage regulator diodes in a common anode configuration
- Working voltage: typ. 6.8 V
- Forward voltage: max. 1.3 V
- Maximum reverse peak power dissipation: 27.5 W at  $t_p = 1 \text{ ms}$
- Maximum clamping voltage at peak pulse current: 11 V at 2.5 A
- Low leakage current: max. 2  $\mu\text{A}$
- ESD rating >8 kV, according IEC 801-2.

**APPLICATIONS**

- Where transient overvoltage protection in voltage and ESD sensitive equipment is required such as:
  - Computers
  - Printers
  - Business machines
  - Communication systems
  - Medical equipment.

**DESCRIPTION**

18-fold monolithic transient voltage suppressor. Its 18-fold junction common anode design protects 18 separate lines using only one package. This device is ideal for situations where board space is a premium.

**PINNING**

PIN	DESCRIPTION
1 to 5	cathode ( $k_1$ to $k_5$ )
6 and 16	common anode ( $a_1$ ; $a_2$ )
7 to 15	cathode ( $k_6$ to $k_{14}$ )
17 to 20	cathode ( $k_{15}$ to $k_{18}$ )

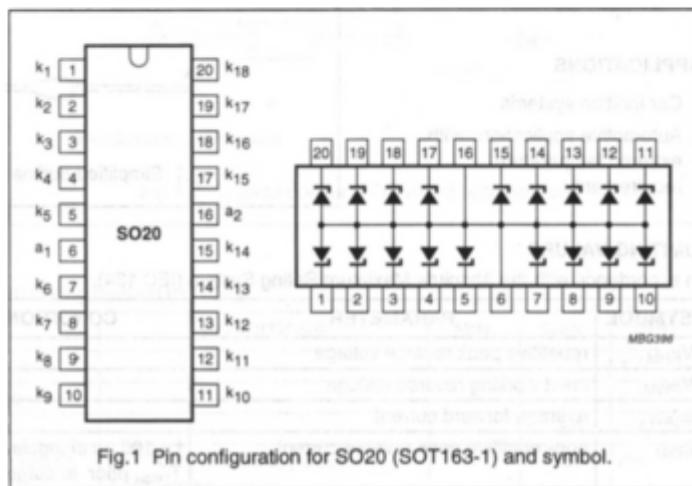


Fig.1 Pin configuration for SO20 (SOT163-1) and symbol.

**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$I_Z$	working current		–	note 1	mA
$I_F$	continuous forward current		–	200	mA
$I_{FSM}$	non-repetitive peak forward current	$t_p = 1 \text{ ms}$ ; square pulse	–	4	A
$I_{ZSM}$	non-repetitive peak reverse current	$t_p = 1 \text{ ms}$ ; square pulse; see Fig.2	–	2.5	A
$P_{tot}$	total power dissipation	see Fig.3 up to $T_s = 60^\circ\text{C}$ ; note 2 up to $T_{amb} = 25^\circ\text{C}$ ; note 3	–	1.6	W
$P_{ZSM}$	non-repetitive peak reverse power dissipation	$t_p = 1 \text{ ms}$ ; square pulse; see Fig.4	–	27.5	W
$T_{stg}$	storage temperature		-65	+150	°C
$T_j$	operating junction temperature		–	150	°C

**Notes**

1. DC working current limited by  $P_{tot\ max}$ .
2. One or more diodes loaded;  $T_s$  is the temperature at the soldering point.
3. One or more diodes loaded; device mounted on a printed-circuit board with  $R_{th\ a-s} = 43.5 \text{ K/W}$ .

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## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\text{-j-s}}$	thermal resistance from junction to soldering point	one or more diodes loaded	56.5	K/W
$R_{th\text{-j-a}}$	thermal resistance from junction to ambient		100	K/W

## ELECTRICAL CHARACTERISTICS

 $T_j = 25^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
<b>Per diode</b>						
$V_Z$	working voltage	$I_Z = 5 \text{ mA}$	6.4	6.8	7.2	V
$V_F$	forward voltage	$I_F = 200 \text{ mA}$	—	—	1.3	V
$V_{ZSM}$	non-repetitive peak reverse voltage	$t_p = 1 \text{ ms}; I_{ZSM} = 2.5 \text{ A}$	—	—	11	V
$I_R$	reverse current	$V_R = 5.25 \text{ V}$	—	—	2	$\mu\text{A}$
$r_{diff}$	differential resistance	$I_Z = 1 \text{ mA}$	—	—	40	$\Omega$
		$I_Z = 5 \text{ mA}$	—	—	8	$\Omega$
$S_Z$	temperature coefficient of working voltage	$I_Z = 5 \text{ mA}$	—	3	—	$\text{mV/K}$
$C_d$	diode capacitance	see Fig.5 $V_R = 0; f = 1 \text{ MHz}$ $V_R = 5.25 \text{ V}; f = 1 \text{ MHz}$	—	—	120 60	$\text{pF}$

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## GRAPHICAL DATA

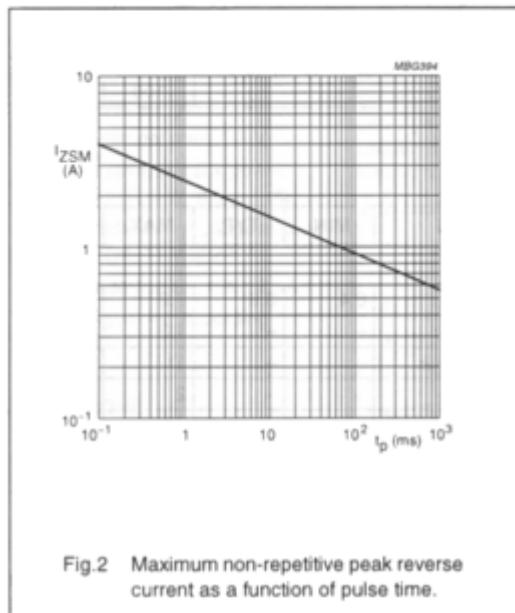
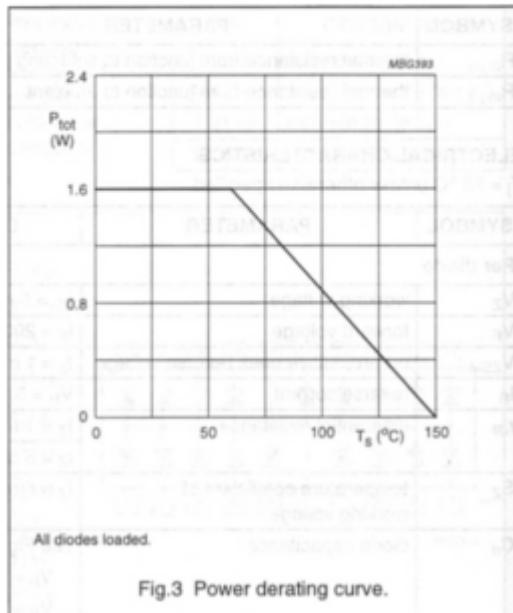


Fig.2 Maximum non-repetitive peak reverse current as a function of pulse time.



All diodes loaded.

Fig.3 Power derating curve.

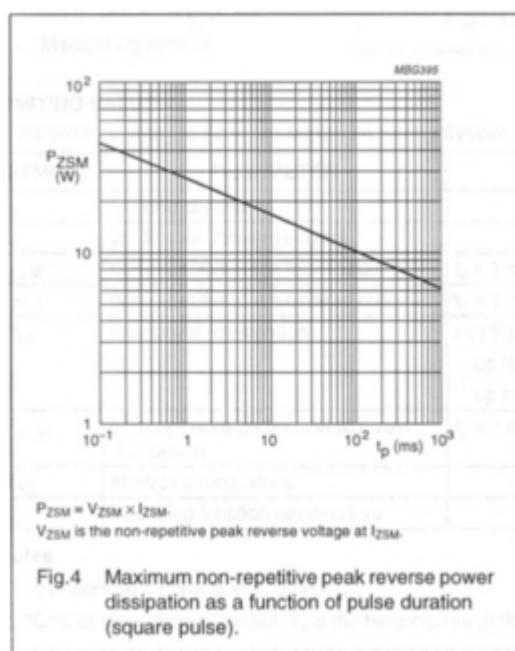


Fig.4 Maximum non-repetitive peak reverse power dissipation as a function of pulse duration (square pulse).

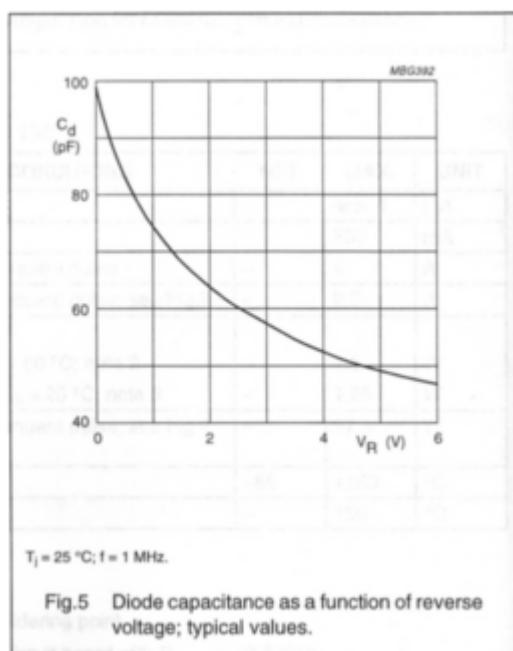


Fig.5 Diode capacitance as a function of reverse voltage; typical values.